"Yت / Descriptions

Silicon NPN transistor in a SOT-323 Plastic Package.

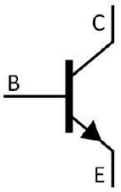
◕È / Features

High current, low voltage complementary pair with BC807W.

¥ ٍ / Applications

General purpose switching and amplification.

Л ف ً ٖ ≠ ع / Equivalent Circuit



ẵ ﻻ ṷ ً / Pinning

PIN1 Emitter PIN 2 Base PIN 3 Collector

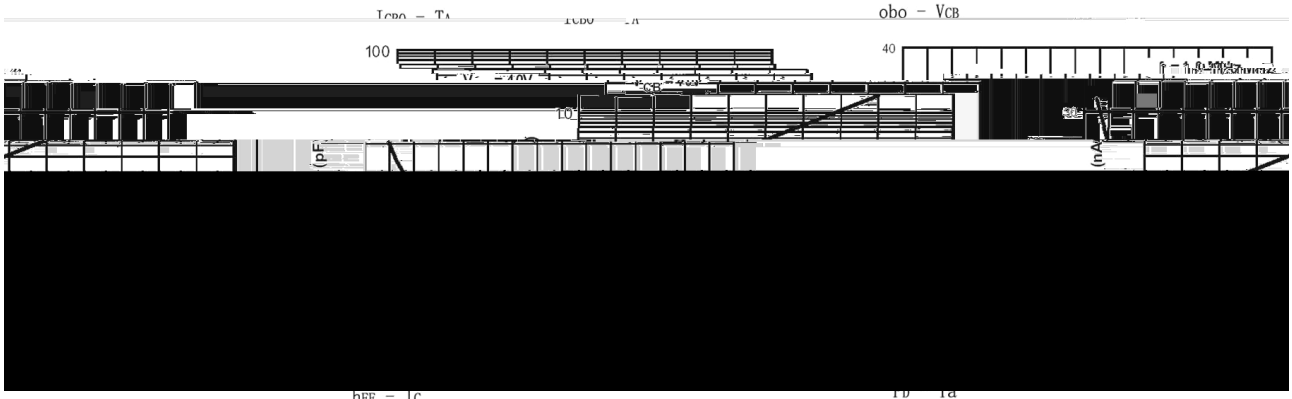
ł. ʜ ڈ / Marking

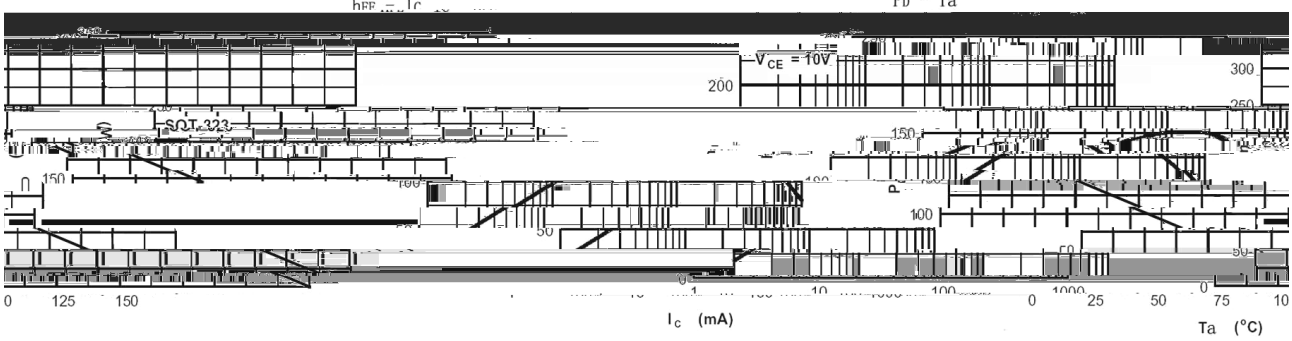
h_{FE} Classifications Symbol	16	25	40
h_{FE} Range	100 250	160 400	250 600
Marking	H6A	H6B	H6C

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	45	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	500	mA
Peak Collector Current - Continuous	I_{CM}	1.0	A
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=20V I_E=0			5.0	μA
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			0.1	μA
DC Current Gain	h_{FE}	V_{CE}=1.0V I_C=100mA	100		600	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA I_B=50mA			0.7	V
Base to Emitter Voltage	V_{BE}	V_{CE}=1.0V I_C=500mA			1.2	V

≠ Ǝ ÃΆ´E ¼ ƒ / Electrical Characteristic Curve

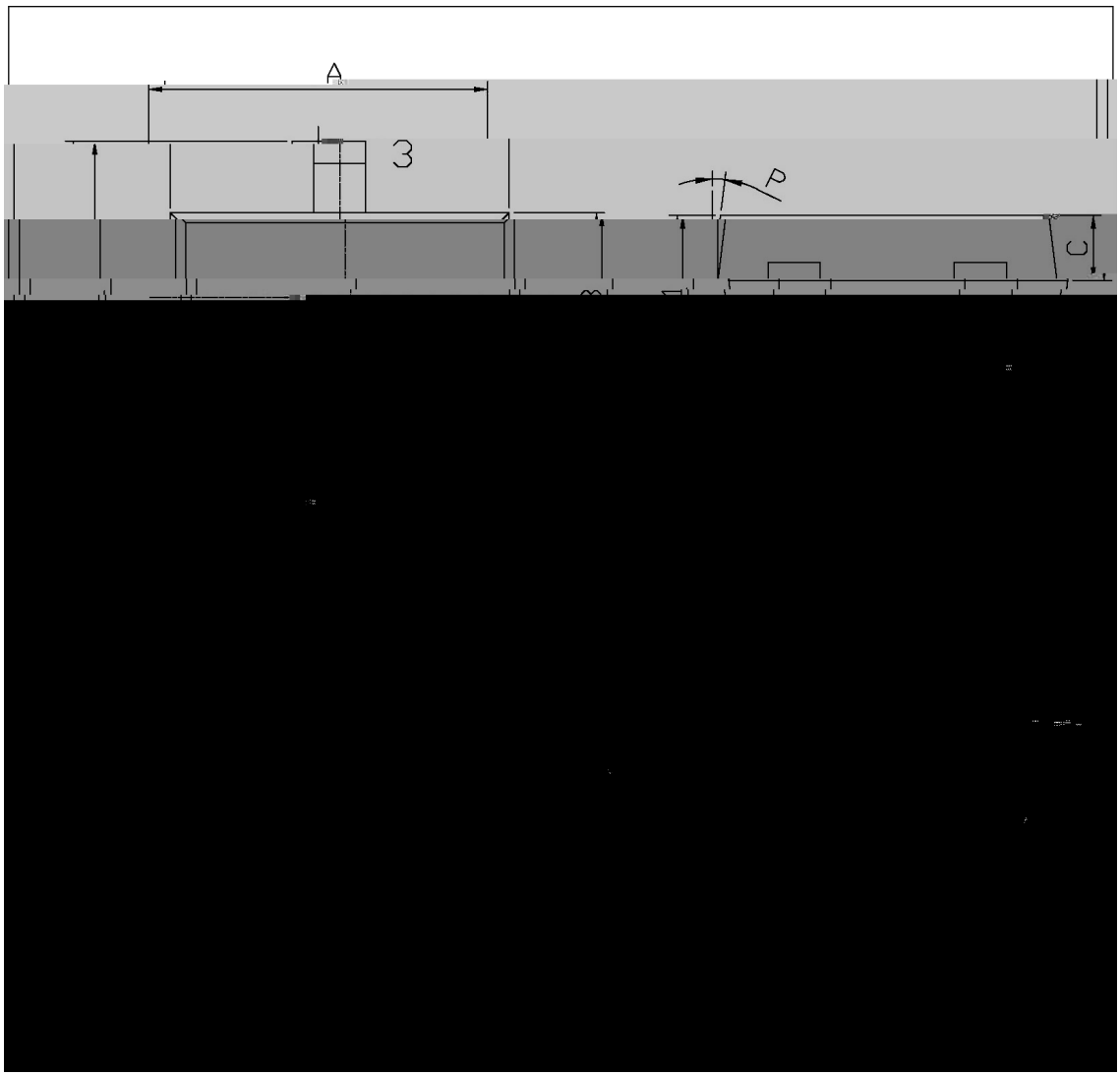




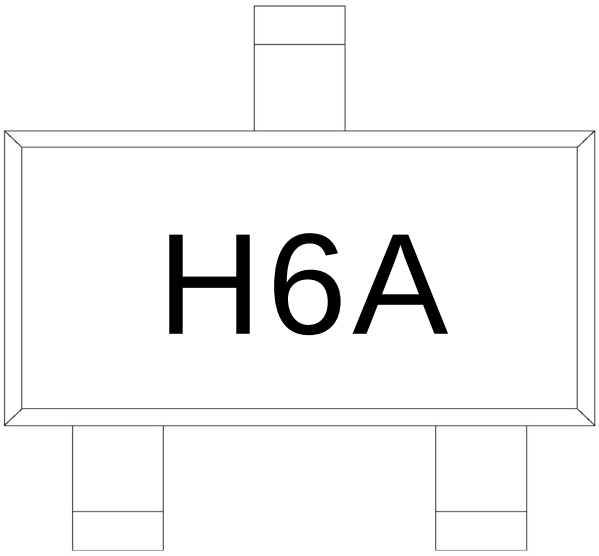
ᵘ Ė Ồ Ļ ʄ / Package Dimensions

SOT-323

单位：mm



Ł. Ł Ω / Marking Instructions



H

6A

Note:

H: Company Code.

6A: Product Type.

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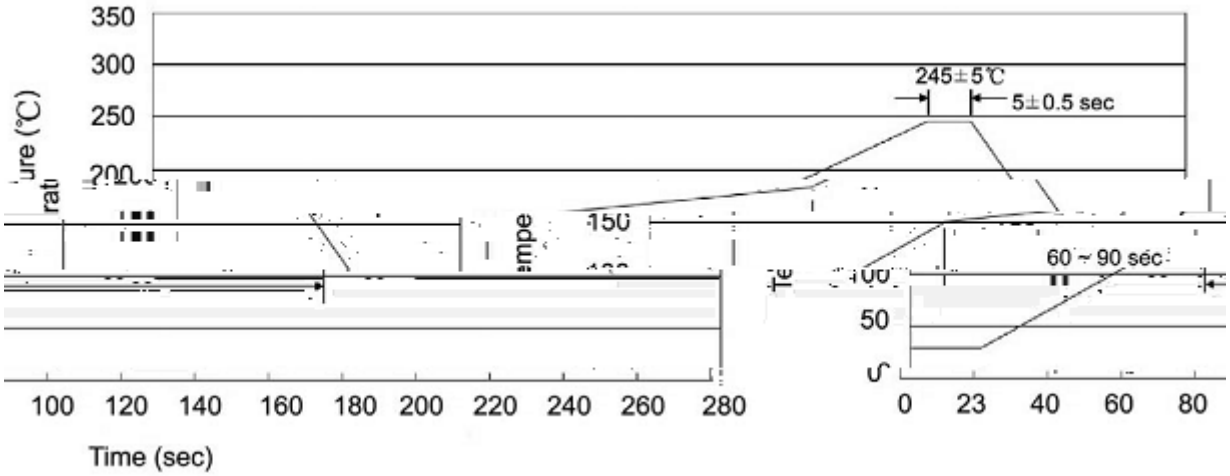

Note:

1		25	150		60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2		245	5			5 0.5sec;	2.Peak Temp.:245 5 , Duration:5 0.5sec.
3				2	10	/sec.	3. Cooling Speed: 2~10 /sec.

⅃ ü q ¯ `Y Ţ / Resistance to Soldering Heat Test Conditions

260 5	10 1 sec.	Temp.:260±5	Time:10±1 sec

ɔ Ł ≮ — / Packaging SPEC.

/ REEL

Package Type	Units					Dimension		(unit mm^3)

ä ⅴ Ļ Ω / Notices